

WHAT IS CLAIMED IS:

1           1.    A semiconductor device comprising:  
2            a.    a leadframe including a plurality of leads extending therefrom, a first  
3    source attach area on a first surface of the leadframe and a first gate attach area, and a second  
4    source attach area on a second surface of the leadframe and a second gate attach area;  
5           b.    at least two dies, a first of which is coupled to the first source and gate  
6    attach areas and a second of which is coupled to the second source and gate attach areas;  
7           c.    a drain connection assembly coupled to a drain region of the first die;  
8    and,  
9           a body, the body being coupled to the semiconductor device such that a drain  
10   region of the second die is exposed.

1           2.    A semiconductor device in accordance with claim 1 wherein at least  
2    one of the dies is a bumped die.

1           3.    A semiconductor device in accordance with claim 2 wherein both dies  
2    are bumped dies.

1           4.    A semiconductor device in accordance with claim 1 wherein the drain  
2    connection assembly comprises a drain clip and a lead rail adjacent an edge of the drain clip.

1           5.    A method of making a semiconductor device, the method  
2    comprising:  
3           providing a leadframe including a plurality of leads extending therefrom, a  
4    first source attach area on a first surface of the leadframe and a first gate attach area, and a  
5    second source attach area on a second surface of the leadframe and a second gate attach area;  
6           bonding a first die to the first source and gate attach areas with solder;  
7           reflowing the solder;  
8           bonding a second die to the second source and gate attach areas with second  
9    solder;  
10          bonding a drain connection assembly to a drain region of the second die with  
11   third solder;  
12          reflowing at least the third solder; and  
13          coupling a body to the semiconductor device such that a drain region of the  
14   second die is exposed.

1                   6.     A method in accordance with claim 5 further comprising reflowing the  
2     second solder prior to bonding the drain connection assembly to the drain region of the  
3     second die.